3-25-05

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	SASAKI et al.	Examiner:	Unknown
Serial No.:	10/522,488	Group Art Unit:	Unknown
Filed:	January 26, 2005	Docket No.:	10873.1623USWO
Title:	METHOD FOR PRODUCING GROUP-III-ELEMENT NITRIDE SINGLE CRYSTAL AND GROUP-III-ELEMENT NITRIDE TRANSPARENT SINGLE CRYSTAL PREPARED THEREBY		

CERTIFICATE UNDER 37 CFR 1.10:
"Express Mail" mailing label number: EV 495870527 US
Date of Deposit: March 23, 2005

I hereby certify that this paper or fee is being deposited with the U.S. Postal Service "Express Mail Post Office to Addressee" service under 37 CFR 1.10 on the date indicated above and is addressed to: Mail Stop Amendment, Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

By: _____
Name: David Ortiz

INFORMATION DISCLOSURE STATEMENT (37 C.F.R. § 1.97(b))

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

Dear Commissioner:

With regard to the above-identified application, the items of information listed on the enclosed Form 1449 are brought to the attention of the Examiner.

This statement should be considered because it is submitted within three months of the filing date of the above-identified application, which is not an application under 37 C.F.R. § 1.53(d). Accordingly, no fee is due for consideration of the items listed on the enclosed Form 1449.

A copy of any foreign patent document or "Other Document" listed on the Form 1449 is enclosed, in accordance with 37 C.F.R. §1.98(a)(2). Because this application was filed after June 30, 2003, copies of the U.S. Patents and U.S. patent publications listed on the enclosed Form 1449 are not provided.

No representation is made that a reference is "prior art" within the meaning of 35 U.S.C. §§ 102 and 103 and Applicants reserve the right, pursuant to 37 C.F.R. § 1.131 or otherwise, to

establish that the references are not "prior art." Moreover, Applicants do not represent that a reference has been thoroughly reviewed or that any relevance of any portion of a reference is intended.

Consideration of the items listed is respectfully requested. Pursuant to the provisions of M.P.E.P. 609, it is requested that the Examiner return a copy of the attached Form 1449, marked as being considered and initialed by the Examiner, to the undersigned with the next official communication.

Please charge any additional fees or credit any overpayment to Deposit Account No. 13-2725.

Respectfully submitted,

MERCHANT & GOULD P.C.
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Minneapolis, Minnesota 55402-0903
(612) 332-5300

Dated: March 23, 2005

By: _____
Douglas P. Mueller
Reg. No. 30,300

DPM/sbd

Date Mailed: March 23, 2005

FORM 1449* INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION (Use several sheets if necessary)	Docket Number: 10873.1623USWO	Application Number: 10/522,488
	Applicant: SASAKI et al.	
	Filing Date: January 26, 2005	Group Art Unit: Unknown

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	5,868,837	02/1999	DiSalvo et al.			
	6,001,748	12/1999	Tanaka et al.			
	6,270,569	08/2001	Shibata et al.			
	2002/0046695	04/2002	Sarayama et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
	0 811 708	12/1997	Europe				
	1288079	03/2001	China			Abstract	
	01/24921	04/2001	WIPO				
	1 278 233	01/2003	Europe				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

		Grzegory et al., "III-V Nitrides-Thermodynamics and Crystal Growth at High N_2 Pressure", Journal of Physics and Chemistry of Solids (1995); 56: 639-647
		Song et al., "Bulk GaN single crystals: growth conditions by flux method", Journal of Crystal Growth (2003); 247: 275-278
		Morishita et al., "Growth of bulk GaN single crystals in metal-sodium flux system", Journal of Japanese Association for Crystal Growth (2002); 29: 119-120
		Extended Abstracts (The 63rd Autumn Meeting, 2002); The Japan Society of Applied Physics No. 0 and No. 1
		Proceedings of the 47th Symposium of Synthetic Crystals, "LPE growth of GaN single crystal and LPE growth using Na-Ca-mixed flux", pp. 87-88
		Kawamura et al., "Synthesis of Bulk GaN Single Crystals Using Na-Ca Flux", Japanese Journal of Applied Physics (2002); 41: 1440-1442

EXAMINER	DATE CONSIDERED

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.